IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Takeshi AKATSU et al.	Confirmation No.: 2732
Application No.: 10/827,437	Patent No.: 7,232,488 B2
Filing Date: April 20, 2004	Patent Date: June 19, 2007
For: METHOD OF FABRICATION OF A SUBSTRATE FOR AN EPITAXIAL GROWTH	Attorney Docket No.: 4717-13000

REQUEST FOR CERTIFICATE OF CORRECTION UNDER 37 C.F.R. § 1.322

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Patentees hereby respectfully request the issuance of a Certificate of Correction in connection with the above-identified patent. The corrections are listed on the attached Form PTO-1050. The corrections requested are as follows:

At column 12, line 28 (claim 18, line 1), delete "**14**" and insert -- **13** --. In the Examiner's Amendment attached to the Notice of Allowability mailed April 17, 2007, application claim 20 was amended to depend from claim 14. Application claim 14 has been renumbered as patent claim 13. Therefore, claim 18 should depend from claim 13.

The requested correction is for an error that appears to have been made by the Office. Therefore, no fee is believed to be due for this request. Should any fees be required, however, please charge such fees to Winston & Strawn LLP Deposit Account No. 50-1814. Please issue a Certificate of Correction in due course.

Respectfully submitted,

6-27-07
Date

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UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO.: 7,232,488 B2
APPLICATION NO.: 10/827,437
DATED: June 19, 2007
INVENTOR(S): Akatsu et al.

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 12:
Line 28 (claim 18, line 1), delete "**14**" and insert -- **13** --.

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the auxiliary substrate to the carrier substrate is conducted in a manner to provide a dislocation density in the transferred portion that is lower than that of the epitaxial base layer on the auxiliary substrate.

10. The method of claim **1**, wherein the further grown portion of the epitaxial base layer comprises silicon germanium.

11. The method of claim **1**, which further comprises transferring one or more additional portions of the further-grown epitaxial base layer from the carrier substrate to one or more further substrates.

12. The method of claim **11**, which further comprises at least one of re-claiming and planarizing the second portion.

13. A method of producing a substrate for conducting epitaxial growth thereon, which comprises:

obtaining a substantially relaxed epitaxial base layer on an auxiliary substrate;

transferring at least a portion of the substantially-relaxed epitaxial base layer onto a carrier substrate to provide a base substrate;

increasing the thickness of the transferred epitaxial base layer portion on the carrier substrate by epitaxial growth to form a further-grown epitaxial base layer thereon while maintaining a high degree of thermodynamic and crystallographic stability of the grown epitaxial base layer;

growing at least one second epitaxial layer on the further grown portion that is associated with the carrier substrate; and

transferring a combination of at least a portion of the epitaxial base layer together with at least a portion of the second epitaxial layer to another substrate.

14. The method of claim **13**, wherein the at least one second epitaxial layer comprises silicon.

15. The method of claim **13**, wherein the at least one second epitaxial layer has a thickness of about 10 nm to about 20 nm.

16. A method of producing a substrate for conducting epitaxial growth thereon, which comprises:

obtaining a substantially relaxed epitaxial base layer on an auxiliary substrate;

transferring at least a portion of the substantially-relaxed epitaxial base layer onto a carrier substrate to provide a base substrate;

increasing the thickness of the transferred epitaxial base layer portion on the carrier substrate by epitaxial growth to form a further-grown epitaxial base layer thereon while maintaining a high degree of thermodynamic and crystallographic stability of the grown epitaxial base layer;

growing at least one second epitaxial layer on the further grown portion that is associated with the carrier substrate;

growing an additional epitaxial base layer of the same material as the transferred epitaxial base layer on the second epitaxial layer; and

transferring a combination of at least a portion of the additional epitaxial base layer together with at least a portion of the second epitaxial layer and together with at least a portion of the epitaxial base layer to another substrate.

17. The method of claim **16**, wherein the second epitaxial layer is made of a different material from the transferred epitaxial base layer, and the additional epitaxial base layer is grown to provide a repeating structure with layers of materials arranged in an alternating sequence.

18. The method of claim **14**, further comprising finishing a surface of the transferred combination to enhance its surface properties. 13

19. The method of claim **10** wherein the substantially relaxed epitaxial base layer on the auxiliary substrate comprises silicon germanium.

20. The method of claim **13**, which further comprises transferring a combination of at least a portion of the additional epitaxial base layer together with at least a portion of the second epitaxial layer to another substrate.

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